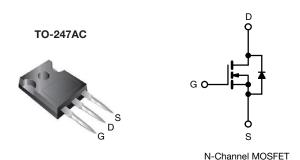


# **Power MOSFET**



PRODUCT SUMMARY			
V <sub>DS</sub> (V)	500		
$R_{DS(on)}(\Omega)$	V <sub>GS</sub> = 10 V 0.60		
Q <sub>g</sub> (max.) (nC)	84		
Q <sub>gs</sub> (nC)	8.4		
Q <sub>gd</sub> (nC)	50		
Configuration	Single		

### **FEATURES**

- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- Isolated Central Mounting Hole
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

#### **DESCRIPTION**

Third Generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-247AC package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220AB devices. The TO-247AC is similar but superior to the earlier TO-218 package because of its isolated mounting hole. It also provides greater creepage distance between pins to meet the requirements of most safety specifications.

ORDERING INFORMATION	
Package	TO-247AC
Lead (Pb)-free	IRFP448PbF

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V <sub>DS</sub>	500	V
Gate-source voltage			V <sub>GS</sub>	± 20	V
Continuous drain current	V <sub>GS</sub> at 10 V	$T_{\rm C} = 25  ^{\circ}{\rm C}$ $T_{\rm C} = 100  ^{\circ}{\rm C}$	1-	11	
Continuous drain current	VGS at 10 V	T <sub>C</sub> = 100 °C	I <sub>D</sub>	6.6	Α
Pulsed drain current <sup>a</sup>			I <sub>DM</sub>	44	
Linear derating factor				1.4	W/°C
Single pulse avalanche energy <sup>b</sup>			E <sub>AS</sub>	550	mJ
Repetitive avalanche current <sup>a</sup>			I <sub>AR</sub>	11	Α
Repetitive avalanche energy a			E <sub>AR</sub>	18	mJ
Maximum power dissipation	T <sub>C</sub> = 25 °C		$P_D$	180	W
Peak diode recovery dV/dt <sup>c</sup>			dV/dt	3.5	V/ns
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	
Soldering recommendations (peak temperature) for 10 s			300 <sup>d</sup>		
Marathan Language			10	lbf ⋅ in	
Mounting torque	6-32 or M3 screw			1.1	N⋅m

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b.  $V_{DD}$  = 50 V, starting  $T_J$  = 25 °C, L = 8.2 mH,  $R_g$  = 25  $\Omega$ ,  $I_{AS}$  = 11 A (see fig. 12)
- c.  $I_{SD} \le 11 \text{ A}$ ,  $dI/dt \le 120 \text{ A/}\mu\text{s}$ ,  $V_{DD} \le V_{DS}$ ,  $T_J \le 150 \,^{\circ}\text{C}$
- d. 1.6 mm from case



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THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R <sub>thJA</sub>	-	40	
Case-to-sink, flat, greased surface	R <sub>thCS</sub>	0.24	-	°C/W
Maximum junction-to-case (drain)	R <sub>thJC</sub>	-	0.70	

PARAMETER	SYMBOL	TEST	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D =$	: 250 μA	500	-	-	V
V <sub>DS</sub> temperature coefficient	$\Delta V_{DS}/T_{J}$	Reference to 2	25 °C, I <sub>D</sub> = 1 mA	-	0.60	-	V/°C
Gate-source threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D =$	= 250 μA	2.0	-	4.0	V
Gate-source leakage	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
Zeve gete veltege dvein evwent	1	V <sub>DS</sub> = 500 V, V	<sub>'GS</sub> = 0 V	-	-	25	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 400 V, V	<sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	250	μA
Drain-source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 6.6 A <sup>b</sup>	-	-	0.60	Ω
Forward transconductance	9 <sub>fs</sub>	$V_{DS} = 50 \text{ V}, I_{D}$	= 6.6 A <sup>b</sup>	6.7	-	-	S
Dynamic							
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V,		-	1900	-	
Output capacitance	C <sub>oss</sub>	$V_{DS} = 25 V$ ,		-	490	-	рF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1.0 MHz, se	f = 1.0 MHz, see fig. 5		220	-	1 .
Total gate charge	Qg		V <sub>GS</sub> = 10 V	-	-	84	
Gate-source charge	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V		-	-	8.4	nC
Gate-drain charge	Q <sub>gd</sub>	see lig. 0 and 13	-	-	50		
Turn-on delay time	t <sub>d(on)</sub>			-	18	-	- ns
Rise time	t <sub>r</sub>	$V_{DD} = 250 \text{ V}, I_{C}$	$V_{DD} = 250 \text{ V}, I_D = 9.6 \text{ A},$		40	-	
Turn-off delay time	t <sub>d(off)</sub>	$R_G = 7.8 \ \Omega, \ R_D = 27 \ \Omega, \ \text{see fig. 10}^{\text{b}}$		-	62	-	
Fall time	t <sub>f</sub>			-	32	-	
Internal drain inductance	L <sub>D</sub>	Between lead,		-	5.0	-	
Internal source inductance	L <sub>S</sub>	, ,	6 mm (0.25") from package and center of		13	-	nН
Drain-Source Body Diode Characteristic	cs						
Continuous source-drain diode current	I <sub>S</sub>	MOSFET symbol showing the integral reverse p - n junction diode		-	-	11	
Pulsed diode forward current <sup>a</sup>	I <sub>SM</sub>			-	-	44	А
Body diode voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub> =	= 11 A, V <sub>GS</sub> = 0 V <sup>b</sup>	-	-	1.7	V
Body diode reverse recovery time	t <sub>rr</sub>			-	480	1100	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	$T_J = 25  ^{\circ}\text{C}, I_F = 9.6  \text{A}, dI/dt = 100  \text{A/} \mu \text{s}^{ \text{b}}$		-	5.2	12	μC
Forward turn-on time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> and I		s and Ln)			

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width  $\leq$  300  $\mu$ s; duty cycle  $\leq$  2 %.



# TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

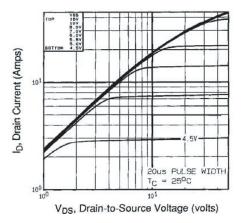


Fig. 1 - Typical Output Characteristics, T<sub>C</sub> = 25 °C

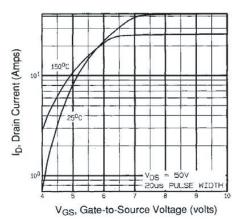


Fig. 3 - Typical Transfer Characteristics

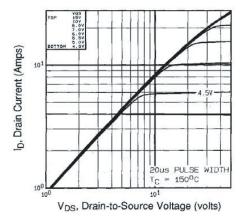


Fig. 2 - Typical Output Characteristics,  $T_C = 150$  °C

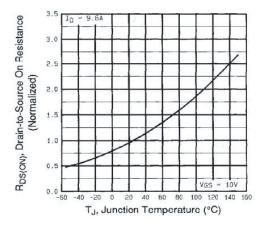


Fig. 4 - Normalized On-Resistance vs. Temperature



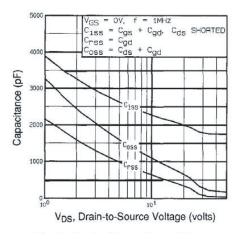


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

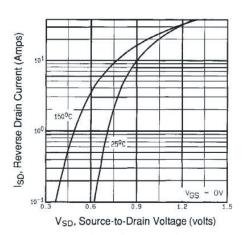


Fig. 7 - Typical Source-Drain Diode Forward Voltage

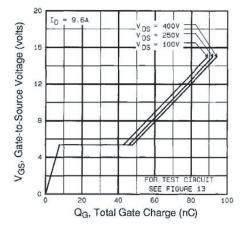


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

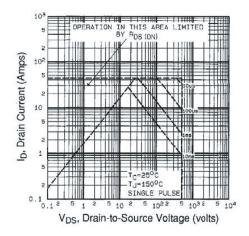


Fig. 8 - Maximum Safe Operating Area



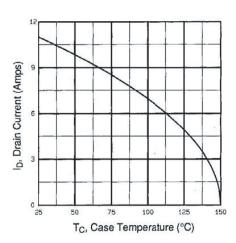


Fig. 9 - Maximum Drain Current vs. Case Temperature

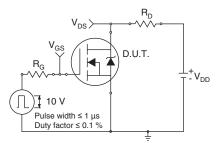


Fig. 10 - Switching Time Test Circuit

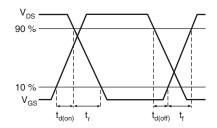


Fig. 11 - Switching Time Waveforms

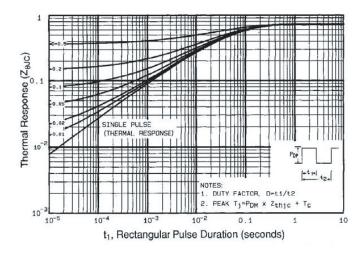
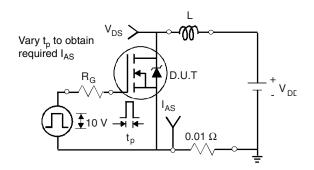


Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case







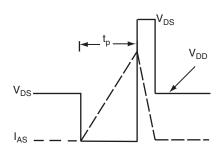


Fig. 14 - Unclamped Inductive Waveforms

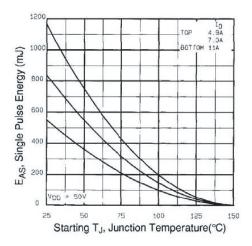


Fig. 15 - Maximum Avalanche Energy vs. Drain Current

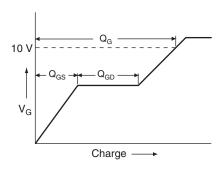


Fig. 16 - Basic Gate Charge Waveform

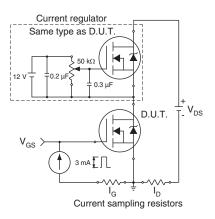
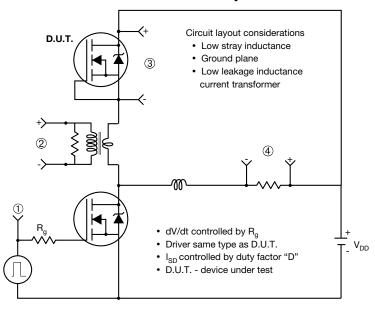


Fig. 17 - Gate Charge Test Circuit



# Peak Diode Recovery dV/dt Test Circuit



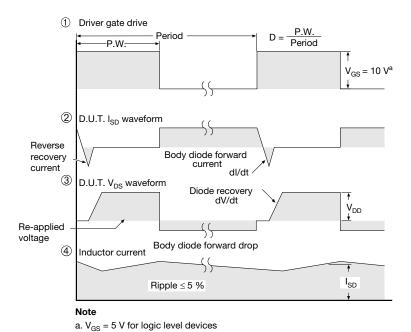


Fig. 18 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?91229">www.vishay.com/ppg?91229</a>.



# **TO-247AC (High Voltage)**

## **VERSION 1: FACILITY CODE = 9**







Section C--C,D--D,E--E

	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
Α	4.83	5.21	
A1	2.29	2.55	
A2	1.50	2.49	
b	1.12	1.33	
b1	1.12	1.28	
b2	1.91	2.39	6
b3	1.91	2.34	
b4	2.87	3.22	6, 8
b5	2.87	3.18	
С	0.55	0.69	6
c1	0.55	0.65	
D	20.40	20.70	4

	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
D1	16.25	16.85	5
D2	0.56	0.76	
E	15.50	15.87	4
E1	13.46	14.16	5
E2	4.52	5.49	3
е	5.44	BSC	
L	14.90	15.40	
L1	3.96	4.16	6
ØΡ	3.56	3.65	7
Ø P1	7.19 ref.		
Q	5.31	5.69	
S	5.54	5.74	

- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- (7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition

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## **VERSION 2: FACILITY CODE = Y**



	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
Α	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIN		
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.254		
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c

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# **VERSION 3: FACILITY CODE = N**



	MILLIM	IETERS
DIM.	MIN.	MAX.
Α	4.65	5.31
A1	2.21	2.59
A2	1.17	1.37
b	0.99	1.40
b1	0.99	1.35
b2	1.65	2.39
b3	1.65	2.34
b4	2.59	3.43
b5	2.59	3.38
С	0.38	0.89
c1	0.38	0.84
D	19.71	20.70
D1	13.08	-

	MILLIMETERS		
DIM.	MIN.	MAX.	
D2	0.51	1.35	
E	15.29	15.87	
E1	13.46	-	
е	5.46	BSC	
k	0.254		
L	14.20	16.10	
L1	3.71	4.29	
N	7.62	BSC	
Р	3.56	3.66	
P1	=	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

ECN: E20-0545-Rev. F, 19-Oct-2020

DWG: 5971

- <sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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